

Description

The SX45P06T uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -60V$ $I_D = -45A$

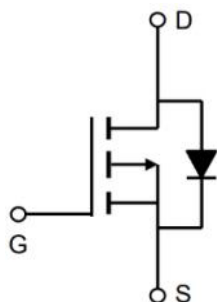
$R_{DS(ON)} < -25m\Omega$ @ $V_{GS} = -10V$

Application

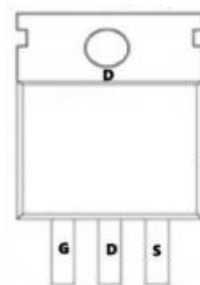
Lithium battery protection

Wireless impact

Mobile phone fast charging



TO-263-3L



Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-60	V
VGS	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$	-45	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$	-28	A
IDM	Pulsed Drain Current ²	-85	A
EAS	Single Pulse Avalanche Energy ³	113	mJ
IAS	Avalanche Current	47.6	A
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ⁴	52.1	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	2.4	$^\circ C/W$

Electrical Characteristics (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60	-68	---	V
ΔBVDSS/ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA	---	-0.035	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-10A	---	20	25	mΩ
		V _{GS} =-4.5V , I _D =-8A	---	26	33	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	-1.6	-2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	4.28	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =-48V , V _{GS} =0V , T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =-10V , I _D =-18A	---	23	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	7	---	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-20V , V _{GS} =-4.5V , I _D =-12A	---	25	---	nC
Q _{gs}	Gate-Source Charge		---	6.7	---	
Q _{gd}	Gate-Drain Charge		---	5.5	---	
Td(on)	Turn-On Delay Time	V _{DD} =-15V , V _{GS} =-10V , R _G =3.3Ω , I _D =-1A	---	38	---	ns
T _r	Rise Time		---	23.6	---	
Td(off)	Turn-Off Delay Time		---	100	---	
T _f	Fall Time		---	6.8	---	
C _{iss}	Input Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz	---	3635	---	pF
C _{oss}	Output Capacitance		---	224	---	
Crss	Reverse Transfer Capacitance		---	141	---	
I _s	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	-35	A
ISM	Pulsed Source Current ^{2,5}		---	---	-70	A
VSD	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C	---	---	-1	V

Note :

- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、 The EAS data shows Max. rating . The test condition is VDD=-48V,VGS =-10V,L=0.1mH,IAS =-47.6A
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Typical Characteristics

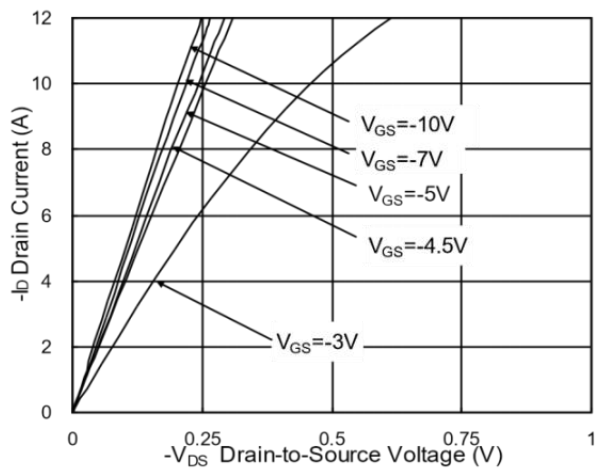


Fig.1 Typical Output Characteristics

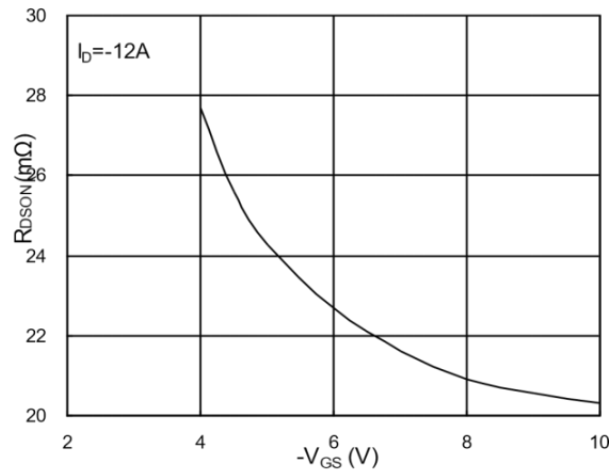


Fig.2 On-Resistance v.s Gate-Source

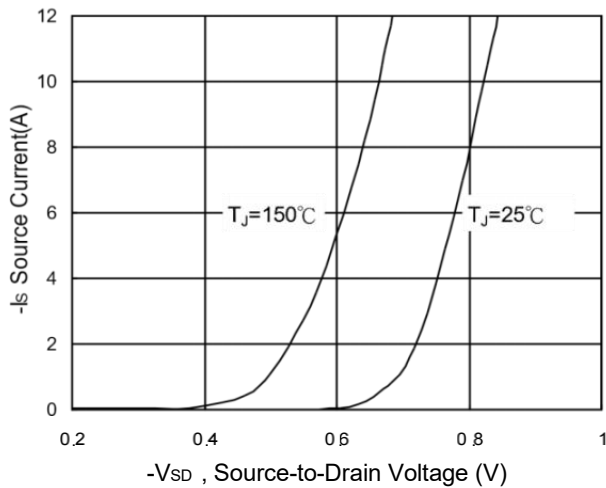


Fig.3 Forward Characteristics Of Reverse

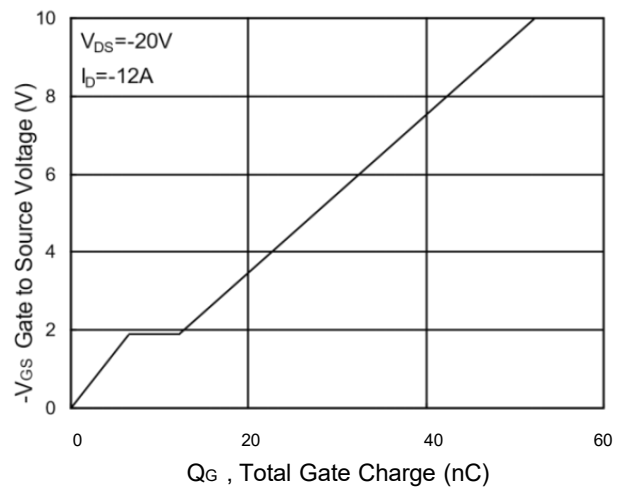


Fig.4 Gate-Charge Characteristics

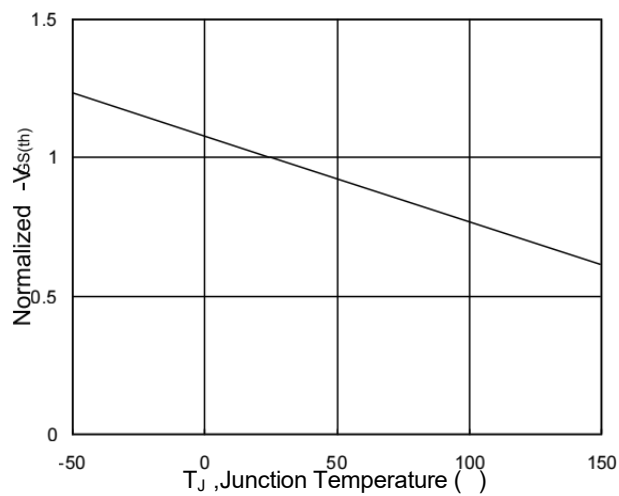


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

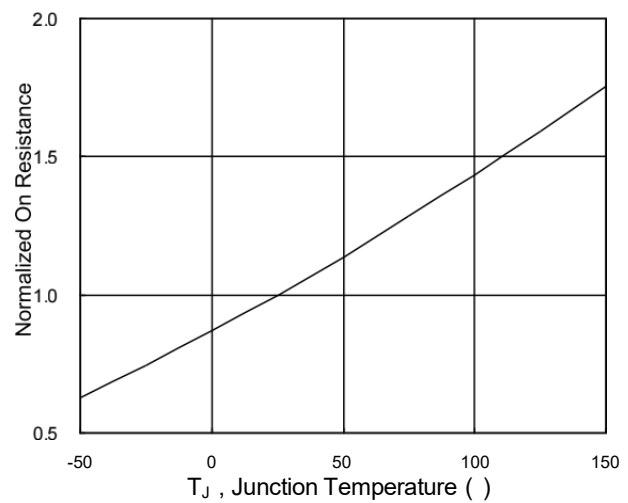


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

Typical Characteristics

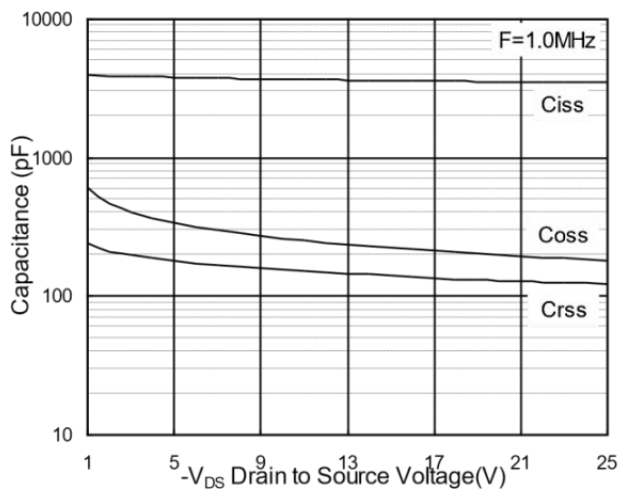


Fig.7 Capacitance

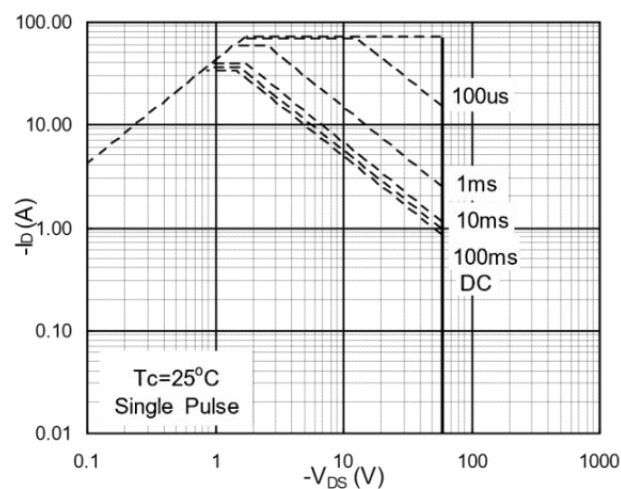


Fig.8 Safe Operating Area

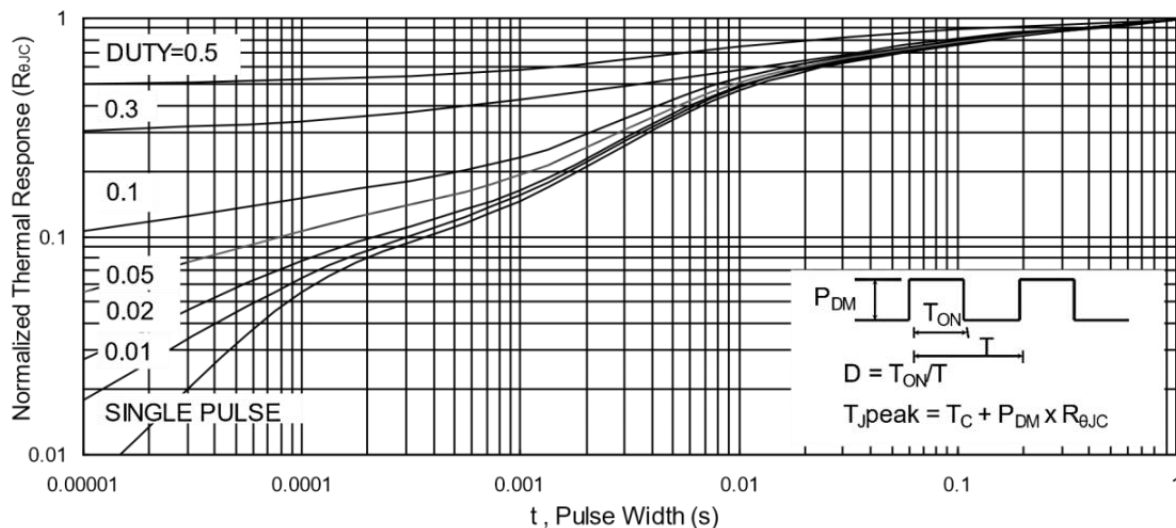


Fig.9 Normalized Maximum Transient Thermal Impedance

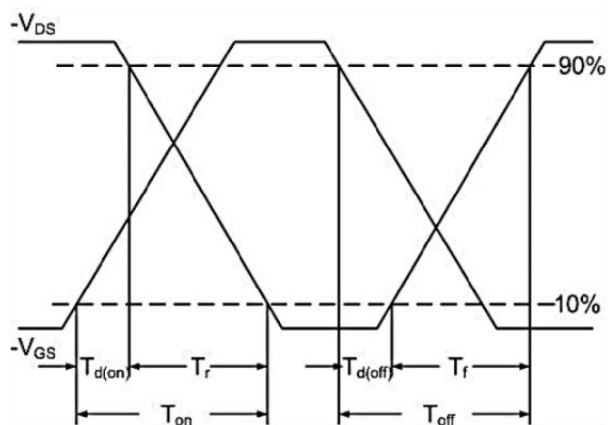


Fig.10 Switching Time Waveform

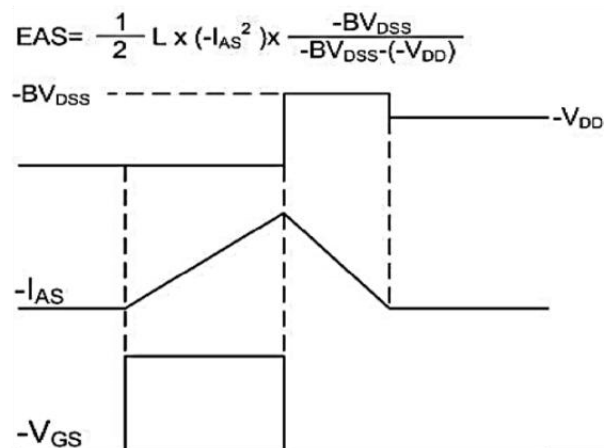
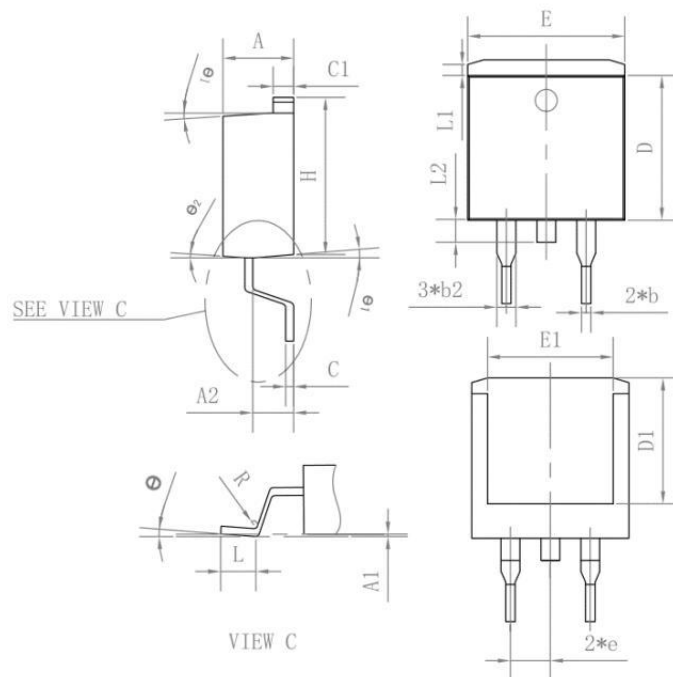


Fig.11 Unclamped Inductive Waveform

Package Mechanical Data-TO-263-3L-SLK


Symbol	Common		
	mm		
	Mim	Nom	Max
A	4.35	4.47	4.60
A1	0.09	0.10	0.11
A2	2.30	2.40	2.70
b	0.70	0.80	1.00
b2	1.25	1.36	1.50
C	0.45	0.50	0.65
C1	1.29	1.30	9.40
D	9.10	9.20	9.30
D1	7.90	8.00	8.10
E	9.85	10.00	10.20
E1	7.90	8.00	8.10
H	15.30	15.50	15.70
e	-	2.54	-
L	2.34	2.54	2.74
L1	1.00	1.10	1.20
L2	1.30	1.40	1.50
R	0.24	0.25	0.26
θ	0°	4°	8°
$\Theta 1$	4°	7°	10°
$\Theta 2$	0°	3°	6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-263-3L		800